Substitute form 1449A/PTO	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/825,647
	Filing Date	April 15, 2004
	First Named Inventor	David B. Slater, Jr.
(use as many sheets as necessary)	Group Art Unit	2822
	Examiner Name	Amir Zarabian
Sheet Page 1 of 3	Attorney Docket Number	5308-231DV

OIPE JC145 JUL 08 2005 PATENT & TRADEMARK OFFICE

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